
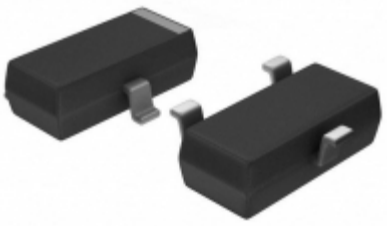
	<p>SI2324DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2324DS-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 100V 2.3A SOT-23</p> <p>Datenblätter:  SI2324DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 140727 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2324DS-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 100V 2.3A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	140727 pcs Stock
detaillierte Beschreibung	N-Channel 100V 2.3A (Tc) 1.25W (Ta), 2.5W (Tc)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	1.25W (Ta), 2.5W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	100V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.3A (Tc)
Rds On (Max) @ Id, Vgs	234 mOhm @ 1.5A, 10V
VGS (th) (Max) @ Id	2.9V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	10.4nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	190pF @ 50V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±20V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI2324DS-T1-GE3-ND

SI2324DS-T1-GE3 ist neu im Original, Suche SI2324DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2324DS-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2324DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2324DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 100V 2.3A SOT-23</p>	 <p>SI2325DS-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 150V 0.53A SOT23-3</p>	 <p>SI2324DS-T1-E3 VISHAY SI2324DS-T1-E3 VISHAY</p>	 <p>SI2325DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 150V 0.53A SOT-23</p>
 <p>SI2323DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 3.7A SOT23-3</p>	 <p>SI2325DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 150V 0.53A SOT-23</p>	 <p>SI2323DS-T1-E3 VIS VIS SOT-23</p>	 <p>SI2324 Vishay Precision Group SI2324 VISHAY</p>

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|--------------------|-------------------|--------------------|--------------------|--------------------|
| ⊛ SI2319DS | ↔ SI2319DS-T1-E3 | ⇒ SI2319DS-T1-E3 | D SI2319DS-T1-GE3 | ↗ SI2319DS-T1-GE3 |
| ⊣ SI2320DS | ⊛ SI2320DS-T1-E3 | D SI2320DS-T1-GE3 | ⇒ SI2321DS-T1-E3 | ↗ SI2321DS-T1-E3 |
| ⊛ SI2321DS-T1-GE3 | ⊣ SI2321DS-T1-GE3 | ⊛ SI2323CDS-T1 | ↔ SI2323CDS-T1-E3 | ↗ SI2323CDS-T1-GE3 |
| D SI2323CDS-T1-GE3 | ⊛ SI2323DDS-T1-E3 | ⊣ SI2323DDS-T1-GE3 | ⊛ SI2323DDS-T1-GE3 | ↗ SI2323DS |
| ⇒ SI2323DS-T1-E3 | ↔ SI2323DS-T1-E3 | ⊛ SI2323DS-T1-GE3 | ⊣ SI2323DS-T1-GE3 | ↗ SI2324DS-T1-E3 |
| ↔ SI2324DS-T1-GE3 | ⇒ SI2325DS-T1-E3 | D SI2325DS-T1-E3 | ⊛ SI2325DS-T1-GE3 | ⊣ SI2325DS-T1-GE3 |
| ⊛ SI2327DS-T1-E3 | D SI2327DS-T1-E3 | ⇒ SI2327DS-T1-GE3 | ↔ SI2327DS-T1-GE3 | ↗ SI2328DS |
| ⊣ SI2328DS-T1 | ⊛ SI2328DS-T1-E3 | ↔ SI2328DS-T1-E3 | ⇒ SI2328DS-T1-GE3 | ↗ SI2328DS-T1-GE3 |
| ⊛ SI2329DS-T1-E3 | ⊣ SI2329DS-T1-GE3 | ⊛ SI2329DS-T1-GE3 | D SI2331DS | ↗ SI2331DS-T1-E3 |
| ↔ SI2331DS-T1-E3 | ⊛ SI2331DS-T1-GE3 | ⊣ SI2331DS-T1-GE3 | ⊛ SI2333ADS-T1-GE3 | ↗ SI2333CDS |

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